

### MOSFET PRODUCT SUMMARY

	$V_{DS}$ (V)	$R_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
<b>N-Channel</b>	30	41 @ $V_{GS} = 10V$	3.0
		45 @ $V_{GS} = 4.5V$	2.2
<b>P-Channel</b>	-30	60 @ $V_{GS} = -10V$	-2.2
		75 @ $V_{GS} = -4.5V$	-1.7

### Features

- Fast switching speed
- High performance trench technology

### Application

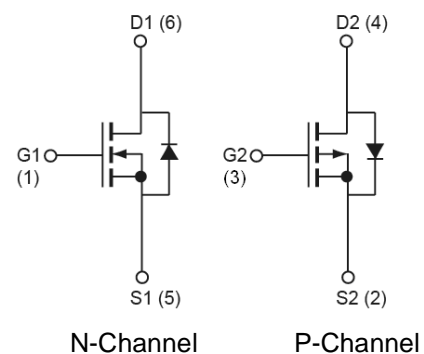
- Load Switch
- PA Switch

### Ordering Information

Part No.	Package	Packing
TSM3548DCX6 RFG	SOT-26	3Kpcs / 7" Reel

**Note:** "G" denote for Halogen Free Product

### Block Diagram



### MOSFET Absolute Maximum Rating ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-CH Limit	P-CH Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	$\pm 12$	V
Continuous Drain Current, <sup>b</sup>	$I_D$	$T_A=25^\circ C$	3.0	-2.2
		$T_A=70^\circ C$	2.4	-1.8
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	12	-8	A
Drain-Source Diode Forward Current <sup>b</sup>	$I_S$	1	-1	A
Power Dissipation <sup>b</sup>	$P_D$	$T_A=25^\circ C$	1.25	1.25
		$T_A=70^\circ C$	0.75	0.75
Operating Junction Temperature	$T_J$	150		$^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ +150		$^\circ C$

### Thermal Performance

Parameter	Symbol	N-CH Limit	P-CH Limit	Unit
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	100	100	$^\circ C/W$

#### Notes:

- Pulse width limited by the Maximum junction temperature
- Surface Mounted on FR4 Board using 1 inch sq pad size,  $t \leq 5$ sec.

**MOSFET Electrical Specifications** (Ta = 25°C unless otherwise noted)

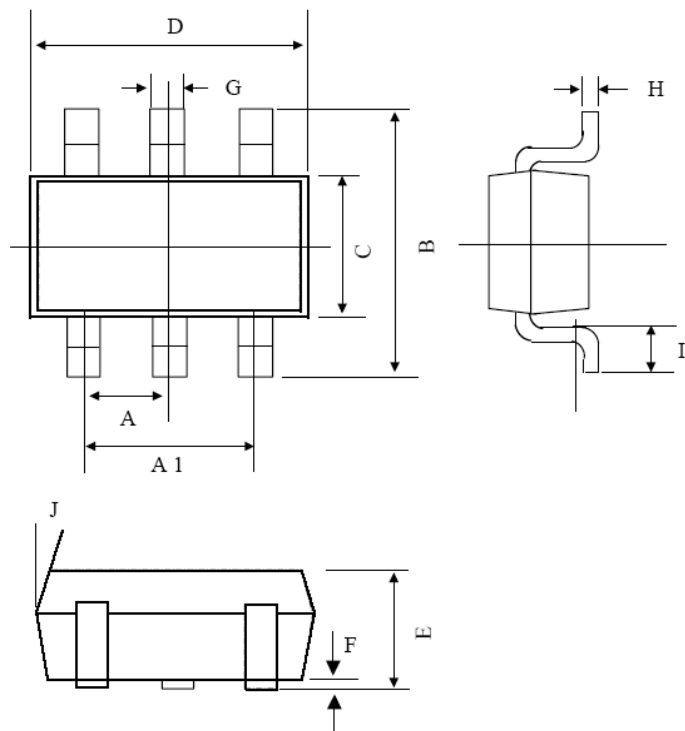
Parameter	Conditions	Symbol	Min	Typ	Max	Unit	
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	BV <sub>DSS</sub>	N-CH	30	--	--	V
	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA		P-CH	-30	--	--	
Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	V <sub>GS(TH)</sub>	N-CH	0.7	0.9	1.4	V
	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA		P-CH	-0.7	-0.9	-1.3	
Gate Body Leakage	V <sub>GS</sub> = 20V, V <sub>DS</sub> = 0V	I <sub>GSS</sub>	N-CH	--	--	±100	nA
	V <sub>GS</sub> = -20V, V <sub>DS</sub> = 0V		P-CH	--	--	±100	
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	I <sub>DSS</sub>	N-CH	--	--	1	μA
	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V		P-CH	--	--	-1	
Drain-Source On-State Resistance <sup>a</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3A	R <sub>DS(ON)</sub>	N-CH	--	31	41	mΩ
	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.2A		P-CH	--	53	60	
	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.2A		N-CH	--	34	45	
	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.7A		P-CH	--	64	75	
<b>Dynamic<sup>b</sup></b>							
Total Gate Charge	N-Channel V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A, V <sub>GS</sub> = 10V	Q <sub>g</sub>	N-CH	--	7	--	nC
			P-CH	--	9.7	--	
Gate-Source Charge	P-Channel	Q <sub>gs</sub>	N-CH	--	1.6	--	
			P-CH	--	1.6	--	
Gate-Drain Charge	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.5A, V <sub>GS</sub> = -10V	Q <sub>gd</sub>	N-CH	--	1.0	--	
			P-CH	--	1.3	--	
Input Capacitance	N-Channel V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	C <sub>iss</sub>	N-CH	--	393	--	pF
			P-CH	--	63	--	
Output Capacitance	P-Channel	C <sub>oss</sub>	N-CH	--	57	--	
			P-CH	--	497	--	
Reverse Transfer Capacitance	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	C <sub>rss</sub>	N-CH	--	62	--	
			P-CH	--	51	--	
<b>Switching<sup>b</sup></b>							
Turn-On Delay Time	N-Channel V <sub>DD</sub> = 15V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 6Ω	t <sub>d(on)</sub>	N-CH	--	7	--	nS
			P-CH	--	6.2	--	
Turn-On Rise Time		t <sub>r</sub>	N-CH	--	10	--	
			P-CH	--	9.5	--	
Turn-Off Delay Time	P-Channel V <sub>DD</sub> = -15V, I <sub>D</sub> = -1A, V <sub>GS</sub> = -10V, R <sub>GEN</sub> = 6Ω	t <sub>d(off)</sub>	N-CH	--	16	--	
			P-CH	--	26	--	
Turn-Off Fall Time		t <sub>f</sub>	N-CH	--	7	--	
			P-CH	--	5.5	--	
Diode Forward Voltage	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	V <sub>SD</sub>	N-CH	--	--	1.1	V
	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V		P-CH	--	--	-1.3	

**Notes:**

a. Pulse test: PW ≤ 300μS, duty cycle ≤ 2%

b. For DESIGN AID ONLY, not subject to production testing.

**SOT-26 Mechanical Drawing**



SOT-26 DIMENSION						
DIM	MILLIMETERS			INCHES		
	MIN	TYP	MAX	MIN	TYP	MAX
A	0.95 BSC			0.0374 BSC		
A1	1.9 BSC			0.0748 BSC		
B	2.60	2.80	3.00	0.1024	0.1102	0.1181
C	1.40	1.50	1.70	0.0551	0.0591	0.0669
D	2.80	2.90	3.10	0.1101	0.1142	0.1220
E	1.00	1.10	1.20	0.0394	0.0433	0.0472
F	0.00	--	0.10	0.00		0.0039
G	0.35	0.40	0.50	0.0138	0.0157	0.0197
H	0.10	0.15	0.20	0.0039	0.0059	0.0079
I	0.30	--	0.60	0.0118	--	0.0236
J	5°	--	10°	5°	--	10°

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